

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of

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Application No.: New Rule 53(b) Continuation
Application of U.S. Application
No. 09/373,982

Filed: June 21, 2001

Docket No.: 036654 D

For: FABRICATION METHOD FOR A THIN FILM SEMICONDUCTOR
DEVICE, THE THIN FILM SEMICONDUCTOR DEVICE ITSELF,
LIQUID CRYSTAL DISPLAY, AND ELECTRONIC DEVICE

PRELIMINARY AMENDMENT

Director of the U.S. Patent and Trademark Office
Washington, D. C. 20231

Sir:

Prior to initial examination, please amend the above-identified application as follows:

IN THE SPECIFICATION:

Page 21, delete lines 4-23, delete the current paragraph and insert therefor:

In the present invention, semiconductor films are deposited on some type of substrates. This is a feature common to all the following inventions. In addition to being applicable to single element films such as silicon (Si) and germanium (Ge), the following types of semiconductor films are also possible: group IV compound semiconductor films such as silicon germanium ($\text{Si}_x\text{Ge}_{1-x}$: $0 < x < 1$), silicon carbide ($\text{Si}_x\text{C}_{1-x}$: $0 < x < 1$), and germanium carbide ($\text{Ge}_x\text{C}_{1-x}$: $0 < x < 1$); III-V compound semiconductor films such as gallium arsenide (GaAs), and indium antimonide (Insb); II-VI compound semiconductor films such as cadmium selenide (CdSe). The present invention is also applicable to higher compound semiconductor films such as silicon germanium gallium arsenide ($\text{Si}_x\text{Ge}_y\text{Ga}_z\text{As}_z$: $x+y+z=1$) as well as N-type semiconductor films in which donor elements such as phosphorous (P),